# NSN 5962-01-481-3808

Memory Microcircuit - Page 1 of 1



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Bodv	Length:

- 1.490 inches
- **Body Width:**

0.610 inches

Body Height:

0.232 inches

**Maximum Power Dissipation Rating:** 

1.0 watts

**Operating Tempurature Range:** 

-55.0/+125.0 degrees celsius

#### Storage Tempurature Range:

-65.0/+150.0 degrees celsius

#### **End Application:**

1430-01-131-5427

#### **Features Provided:**

Monolithic

## Inclosure Configuration:

Dual-in-line

## **Output Logic Form:**

Complementary-metal oxide-semiconductor logic

## **Product Name:**

Microcircuit, digital, memory, cmos, parallel 512 x 9 fifo, monolithic silicon

# Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

## **Time Rating Per Chacteristic:**

65.00 nanoseconds af output megawatts

## Memory Device Type:

First-in first-out

## **Test Data Document:**

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

## Terminal Type And Quantity:

28 printed circuit

#### Shelf Life:

N/a

#### Unit Of Measure:

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## Demilitarization:

Yes - demil/mli

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